

NIR/Red Enhanced 6 mm² Photodiode-Preamplifier



FEATURES

- Large Active Area
- Low Noise
- High Sensitivity
- Custom Gains Available
- · Hermetically Sealed TO-39

Electro-Optical Characteristics at 23°C

Parameters	Test Conditions	Min	Тур	Max	Units
Active Area	3.30 mm x 1.78 mm		5.87		mm ²
Dark Offset	V _s = ±5 V		1	±2	mV
Dark Offset Noise	$V_s = \pm 5$ BW = 0.1 to 135 kHz		283	500	μV rms
Sensitivity	V _s = ±5 V λ = 940 nm	275	315		V/µW
Frequency Response (-3 db)	V _s = ±5 V	100	130		Hz
NEP	λ = 940 nm		1.2		fW/√Hz
Transimpedance Gain			500		ΜΩ
Supply Current			850	950	μΑ

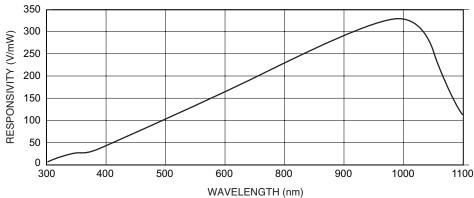
Absolute Ratings

Parameters	Units		
Voltage Supply Range +V to –V*	5 to 15 V		
Power Dissipation	15 mW		
Storage and Operating Temperature	−25 to + 100°C		
Soldering Temperature (1/16" from case for 3 seconds max)	+260°C		

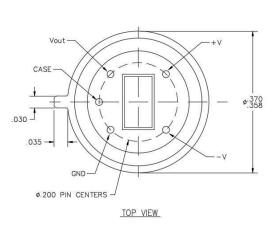
^{*}Voltage supply across the device requires a minimum of 5 V to a maximum of 15 V from +V to -V.

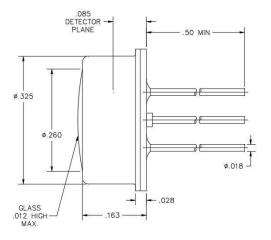
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Typical Spectral Response



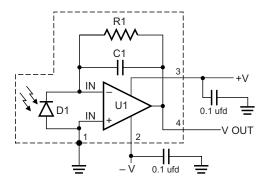
Package Information





ALL DIMENSIONS ARE IN INCH UNITS

Dimensions are in inch [metric] units.



Specifications are subject to change without prior notice.

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